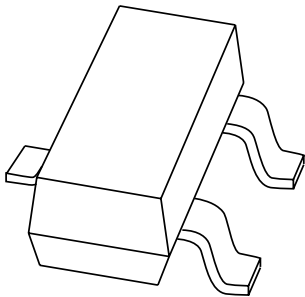


DATA SHEET



BCV71; BCV72 NPN general purpose transistors

Product data sheet
Supersedes data of 1997 Mar 11

1999 Apr 08

NPN general purpose transistors

BCV71; BCV72

FEATURES

- Low current (max. 100 mA)
- Low voltage (max. 60 V).

APPLICATIONS

- General purpose switching and amplification.

DESCRIPTION

NPN transistor in a SOT23 plastic package.

MARKING

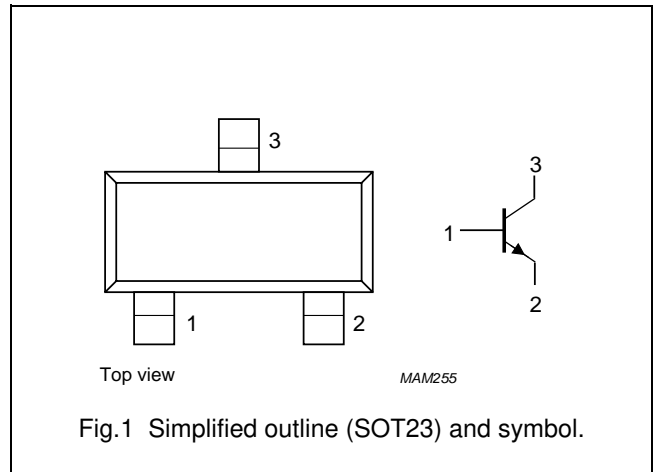
TYPE NUMBER	MARKING CODE ⁽¹⁾
BCV71	K7*
BCV72	K8*

Note

- * = p : Made in Hong Kong.
* = t : Made in Malaysia.

PINNING

PIN	DESCRIPTION
1	base
2	emitter
3	collector



LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CBO}	collector-base voltage	open emitter	–	80	V
V _{CEO}	collector-emitter voltage	open base; I _C = 2 mA	–	60	V
V _{EBO}	emitter-base voltage	open collector	–	5	V
I _C	collector current (DC)		–	100	mA
I _{CM}	peak collector current		–	200	mA
I _{BM}	peak base current		–	200	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	–	250	mW
T _{stg}	storage temperature		–65	+150	°C
T _j	junction temperature		–	150	°C
T _{amb}	operating ambient temperature		–65	+150	°C

NPN general purpose transistors

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THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j-a}$	thermal resistance from junction to ambient	note 1	500	K/W

Note

1. Transistor mounted on an FR4 printed-circuit board.

CHARACTERISTICS

$T_j = 25\text{ °C}$ unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I_{CBO}	collector cut-off current	$I_E = 0; V_{CB} = 20\text{ V}$	–	–	100	nA
		$I_E = 0; V_{CB} = 20\text{ V}; T_j = 100\text{ °C}$	–	–	10	μA
I_{EBO}	emitter cut-off current	$I_C = 0; V_{EB} = 5\text{ V}$	–	–	100	nA
h_{FE}	DC current gain	$I_C = 10\text{ }\mu\text{A}; V_{CE} = 5\text{ V}$	–	90	–	
	BCV71					
	BCV72	–	150	–		
h_{FE}	DC current gain	$I_C = 2\text{ mA}; V_{CE} = 5\text{ V}$	110	–	220	
	BCV71					
	BCV72	200	–	450		
V_{CEsat}	collector-emitter saturation voltage	$I_C = 10\text{ mA}; I_B = 0.5\text{ mA}$	–	120	250	mV
		$I_C = 50\text{ mA}; I_B = 2.5\text{ mA}$	–	210	–	mV
V_{BEsat}	base-emitter saturation voltage	$I_C = 10\text{ mA}; I_B = 0.5\text{ mA}$	–	750	–	mV
		$I_C = 50\text{ mA}; I_B = 2.5\text{ mA}$	–	850	–	mV
V_{BE}	base-emitter voltage	$I_C = 2\text{ mA}; V_{CE} = 5\text{ V}$	550	–	700	mV
C_c	collector capacitance	$I_E = I_B = 0; V_{CB} = 10\text{ V}; f = 1\text{ MHz}$	–	2.5	–	pF
f_T	transition frequency	$I_C = 10\text{ mA}; V_{CE} = 5\text{ V}; f = 100\text{ MHz}$	100	–	–	MHz
F	noise figure	$I_C = 200\text{ }\mu\text{A}; V_{CE} = 5\text{ V}; R_S = 2\text{ k}\Omega;$ $f = 1\text{ kHz}; B = 200\text{ Hz}$	–	–	10	dB

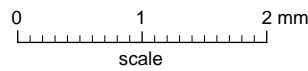
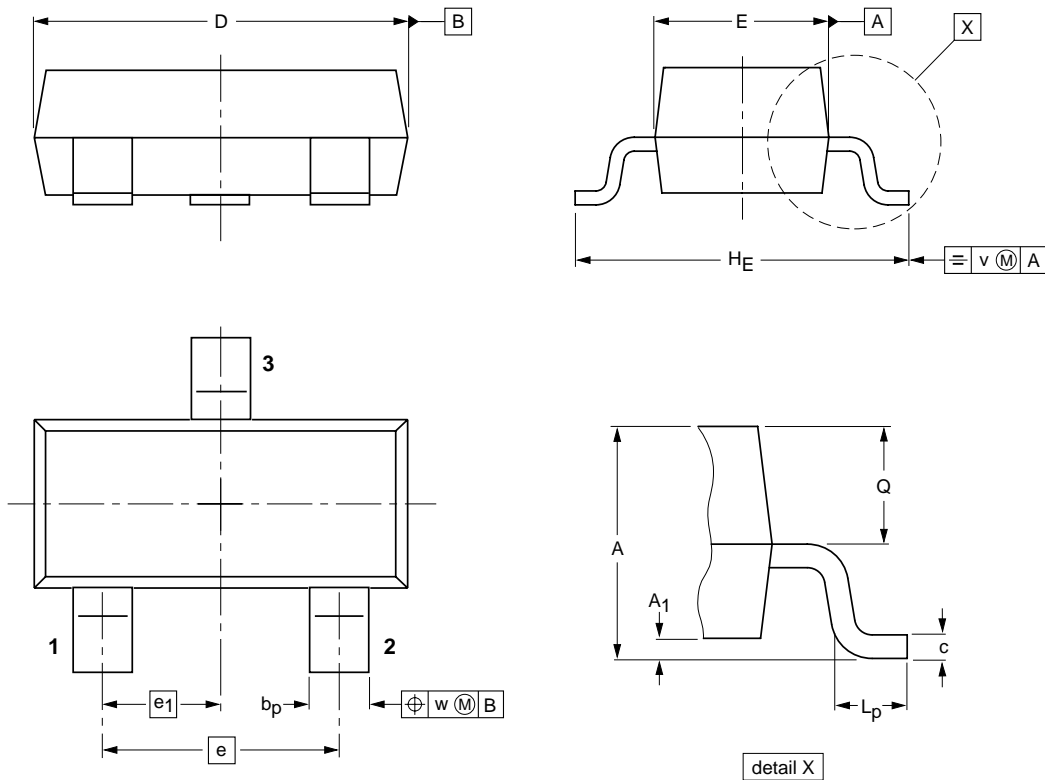
NPN general purpose transistors

BCV71; BCV72

PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT23



DIMENSIONS (mm are the original dimensions)

UNIT	A	A ₁ max.	b _p	c	D	E	e	e ₁	H _E	L _p	Q	v	w
mm	1.1 0.9	0.1	0.48 0.38	0.15 0.09	3.0 2.8	1.4 1.2	1.9	0.95	2.5 2.1	0.45 0.15	0.55 0.45	0.2	0.1

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT23		TO-236AB				97-02-28 99-09-13

NPN general purpose transistors

BCV71; BCV72

DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

Notes

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Customer notification

This data sheet was changed to reflect the new company name NXP Semiconductors, including new legal definitions and disclaimers. No changes were made to the technical content, except for package outline drawings which were updated to the latest version.

Contact information

For additional information please visit: <http://www.nxp.com>

For sales offices addresses send e-mail to: salesaddresses@nxp.com

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